

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. **(currently amended)** A process [[for]] of lapping [[the]] a second side of a wafer, which is provided at [[its]] a first side thereof with [[an]] a ultraviolet tape attached thereto to said first side, said method comprising the steps of:

irradiating the ultraviolet tape attached to the first side of the wafer with ultraviolet light;
maintaining a lapping jig, [[to]] on which the wafer is to be placed, at a temperature higher than a binder's melting temperature but lower than [[the]] a deformation temperature of the ultraviolet tape;

applying the binder to an upper surface of the lapping jig;
bonding the first side of the wafer to the lapping jig via the binder;
placing displacing the lapping jig having the wafer bonded thereto on a lapping plate;
lapping the second side of the wafer to cause [[to]] the wafer to have a predetermined thickness; and
removing the wafer from the lapping jig.

2. **(original)** The process as set forth in claim 1, in which the step of maintaining the lapping jig at the temperature further comprises the step of placing the lapping jig on a hot plate for a predetermined period of time causing its temperature to be maintained at a temperature higher than the binder's melting temperature but lower than a deformation temperature of the ultraviolet tape.

3. (original) The process as set forth in claim 1, in which the binder is Aqua wax.
4. (original) The process as set forth in claim 1, in which the temperature of the lapping jig is maintained within a temperature range of about 45°C to 85°C.

5-10. (*canceled*)

11. **(currently amended)** A method [[for]] of processing a backside of a wafer, said method comprising the steps of:

attaching [[an]] a ultraviolet tape to a front side of the wafer;
grinding the backside of the wafer to cause the wafer to have a first thickness;
irradiating the ultraviolet tape attached to the front side of the wafer with ultraviolet light;
maintaining a lapping jig at a temperature higher than [[the]] a binder's melting temperature but lower than a deformation temperature of the ultraviolet tape;
applying the binder to an upper surface of the lapping jig;
bonding the front side of the wafer to the lapping jig via the binder;
placing ~~displacing~~ the lapping jig having the wafer bonded thereto on a lapping plate;
lapping the backside of the wafer to cause the wafer to have a second thickness;
removing the wafer from the lapping jig; and
removing the ultraviolet tape from the wafer.

12. **(new)** The method of claim 1, wherein said irradiating step is performed before said lapping step.

13. **(new)** The method of claim 12, wherein said irradiating step is performed before said bonding step.

14. (new) The method of claim 1, wherein, in said bonding step, the ultraviolet tape is bonded to the lapping jig via the binder.

15. (new) The method of claim 11, wherein said irradiating step is performed before said lapping step.

16. (new) The method of claim 15, wherein said irradiating step is performed before said bonding step.

17. (new) The method of claim 11, wherein, in said bonding step, the ultraviolet tape is bonded to the lapping jig via the binder.

18. (new) A method of processing a wafer, said method comprising the steps of:
attaching a ultraviolet tape to a first side of the wafer;
irradiating the ultraviolet tape with ultraviolet light to relieve adhesive stress of the ultraviolet tape;
lapping a second, opposite side of the wafer to reduce a thickness of the wafer; and
removing the ultraviolet tape from the wafer;
wherein said irradiating step is performed before said lapping step.

19. (new) The method of claim 18, further comprising bonding the first side of the wafer to a lapping jig via a binder before said lapping and after said irradiating.

20. (new) The method of claim 19, wherein, in said bonding step, the ultraviolet tape is bonded to the lapping jig via the binder.